

ABSTRACT OF THE DISCLOSURE

5 An integrated circuit device that includes a semiconductor substrate, a well region formed inside the semiconductor substrate, a first isolation structure formed inside the well region, a second isolation structure formed inside the well region and spaced apart from the first isolation structure, a dielectric layer formed over the well region, and a layer of silicon, formed over the dielectric layer, including a p-type portion, an n-type portion and a center portion disposed between the p-type and n-type portions.

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